ABSTRACT

An insulating film (3) is formed on a semiconductor substrate (1) having a gate electrode (22) and a source-drain region (12) formed thereon. In the insulating film are formed contact holes (41, 42) such that the upper surfaces of the gate electrode and the adjacent source-drain region are exposed. Conductive plugs (61, 62) are formed in these contact holes. A conductive film is formed just over the conductive plugs and the insulating film. The conductive film is etched to form a lower wiring (7) while a coating (8) consisting of the conductive film is simultaneously formed over the conductive plug (61) which is not connected to the wiring. This process may prevent damages on the conductive plug (61) and may reduce the number of steps required for manufacturing a semiconductor.



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